

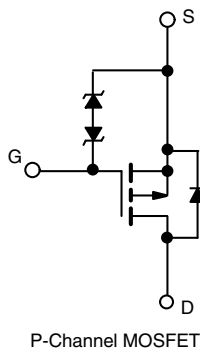
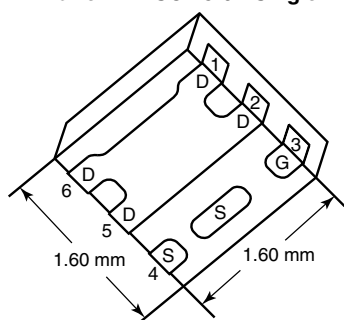


P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)
- 12	0.0255 at V _{GS} = - 4.5 V	- g ^a	13.4 nC
	0.0280 at V _{GS} = - 3.7 V	- g ^a	
	0.0360 at V _{GS} = - 2.5 V	- g ^a	
	0.0600 at V _{GS} = - 1.8 V	- g ^a	
	0.1150 at V _{GS} = - 1.5 V	- 2	

PowerPAK SC-75-6L-Single



Ordering Information:

SiB441EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Performance 2500 V
- 100 % R_g Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

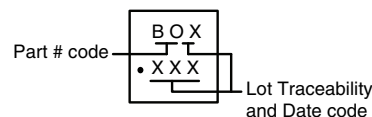


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable Devices such as Smart Phones, Tablet PCs and Mobile Computing
 - Battery Switch
 - Load Switch
 - Power Management

Marking Code



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 12	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current (t = 300 μs)	I _{DM}	- 40	A
Continuous Source-Drain Diode Current	I _S	- 9 ^a	
		- 2 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	41	51	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	7.5	9.5	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.

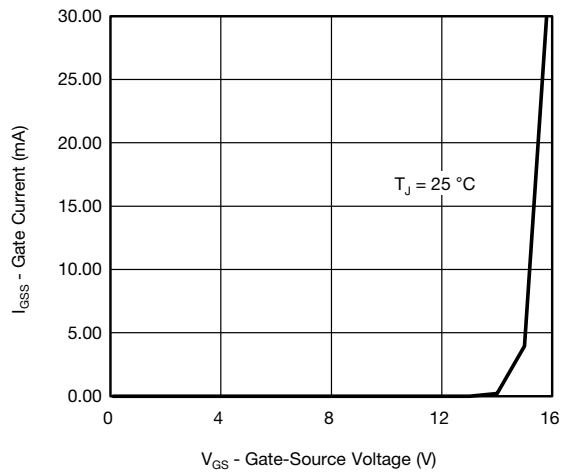
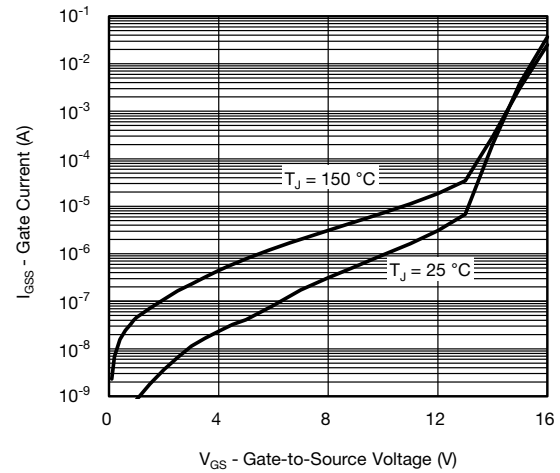
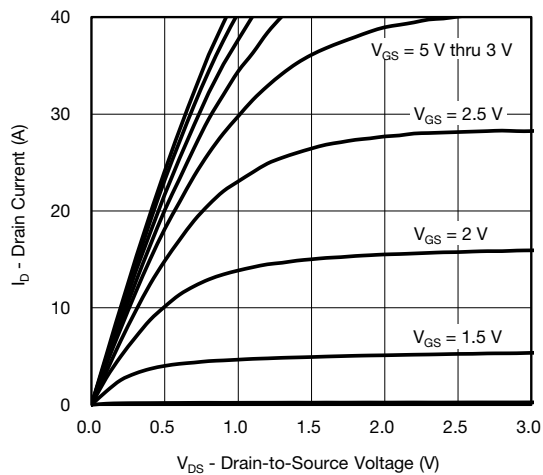
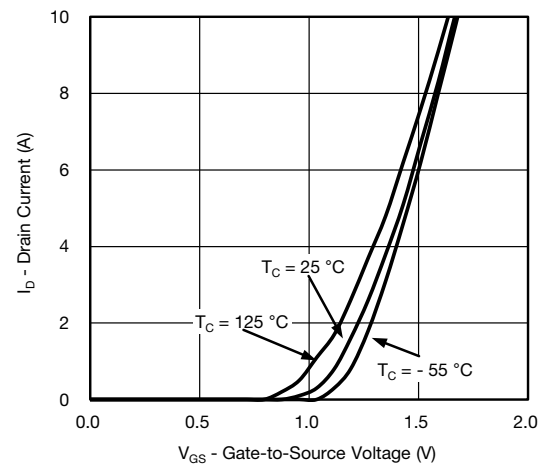
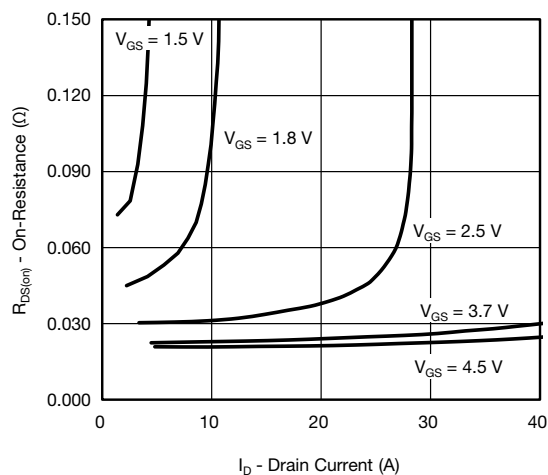
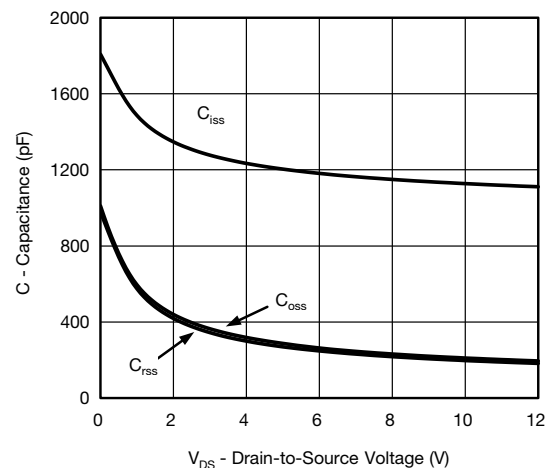
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 12			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 5		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.7			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 0.9	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 4	μA	
		V _{DS} = 0 V, V _{GS} = ± 4.5 V			± 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 15			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 4 A		0.0210	0.0255	Ω	
		V _{GS} = - 3.7 V, I _D = - 4 A		0.0230	0.0280		
		V _{GS} = - 2.5 V, I _D = - 2 A		0.0290	0.0360		
		V _{GS} = - 1.8 V, I _D = - 2 A		0.0420	0.0600		
		V _{GS} = - 1.5 V, I _D = - 0.5 A		0.0570	0.1150		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 6 V, I _D = - 4 A		17		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = - 6 V, V _{GS} = 0 V, f = 1 MHz		1180		pF	
Output Capacitance	C _{oss}			265			
Reverse Transfer Capacitance	C _{rss}			250			
Total Gate Charge	Q _g	V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 2.1 A		22.1	33	nC	
		V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 2.1 A		13.4	20		
Gate-Source Charge	Q _{gs}			1.6			
Gate-Drain Charge	Q _{gd}			3.4			
Gate Resistance	R _g	f = 1 MHz	2.2	11	22	Ω	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 2.7 Ω I _D ≅ - 2.2 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		22	45	ns	
Rise Time	t _r			42	85		
Turn-Off Delay Time	t _{d(off)}			60	120		
Fall Time	t _f			50	100		
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 2.7 Ω I _D ≅ - 2.2 A, V _{GEN} = - 8 V, R _g = 1 Ω		7	15		
Rise Time	t _r			10	20		
Turn-Off Delay Time	t _{d(off)}			60	120		
Fall Time	t _f			52	100		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 9	A	
Pulse Diode Forward Current	I _{SM}				- 40		
Body Diode Voltage	V _{SD}	I _S = - 2.2 A, V _{GS} = 0 V		- 0.85	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 2.2 A, dI/dt = 100 A/μs, T _J = 25 °C		30	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			12	25	nC	
Reverse Recovery Fall Time	t _a			9		ns	
Reverse Recovery Rise Time	t _b			11			

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

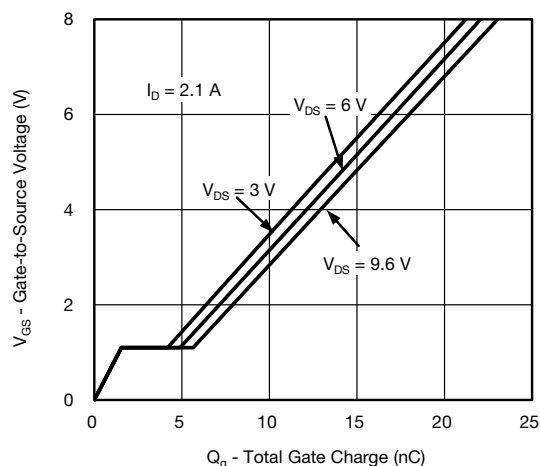
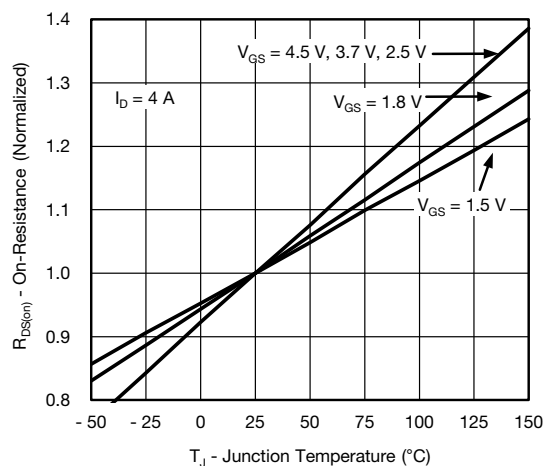
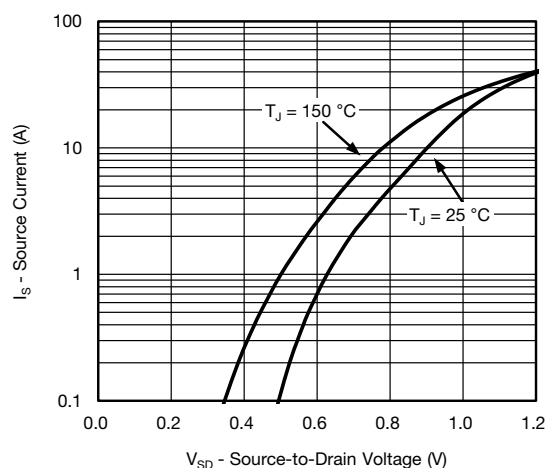
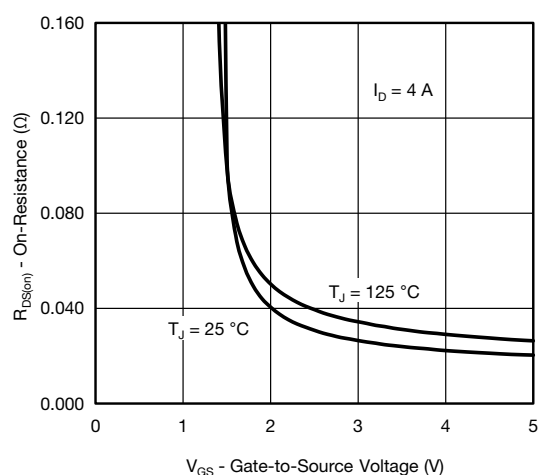
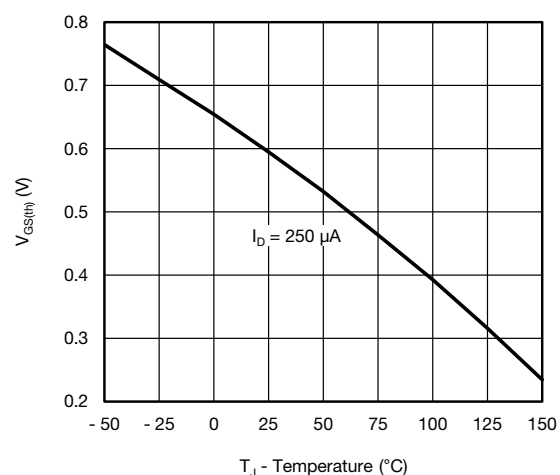
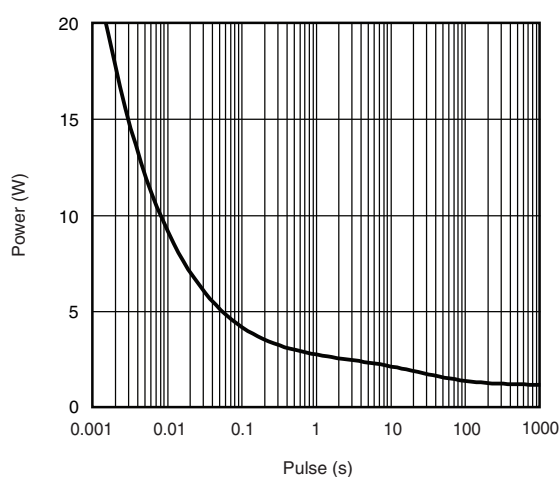
b. Guaranteed by design, not subject to production testing.

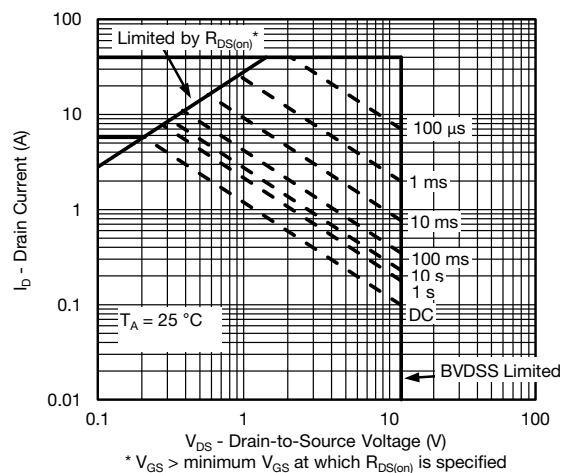
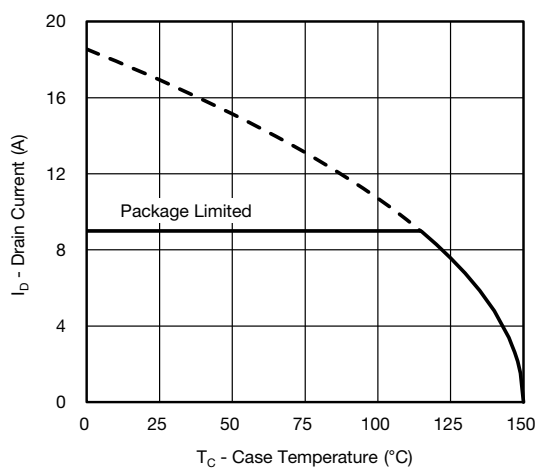
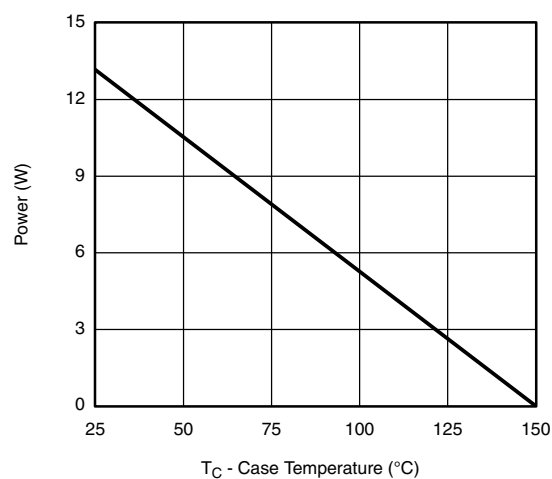
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Gate Current vs. Gate-Source Voltage

Gate Current vs. Gate-Source Voltage

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

SiB441EDK

Vishay Siliconix

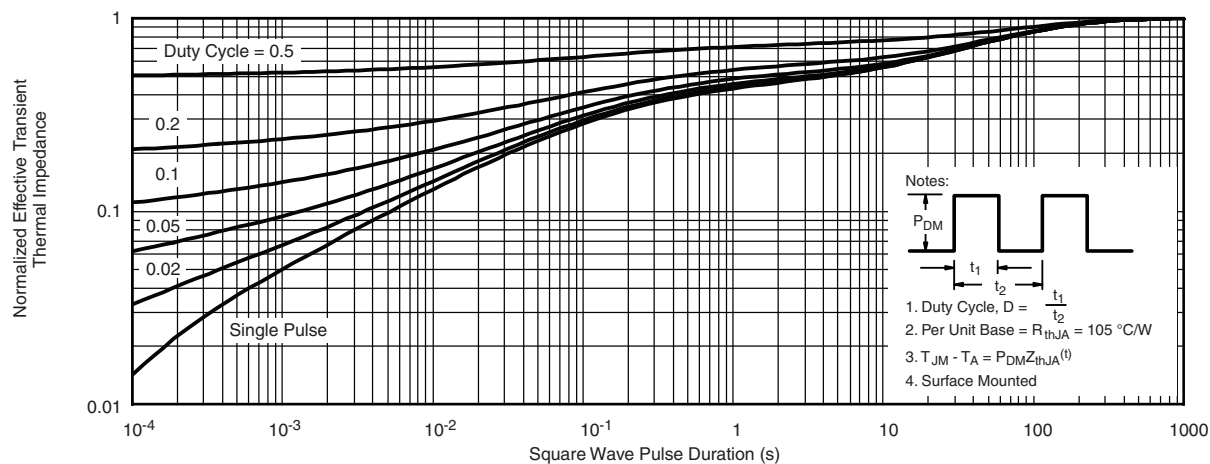
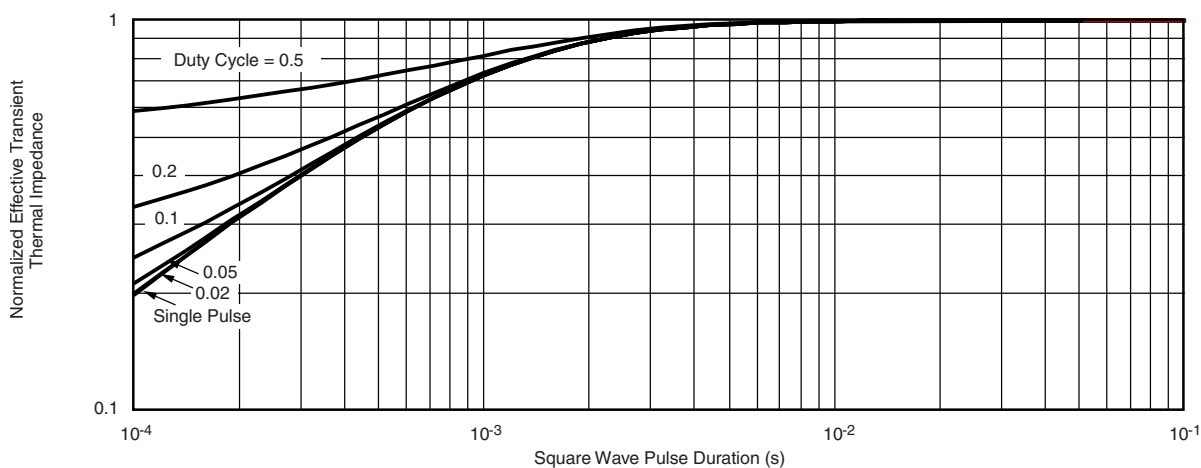
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Safe Operating Area, Junction-to-Ambient****Current Derating*****Power Derating**

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiB441EDK

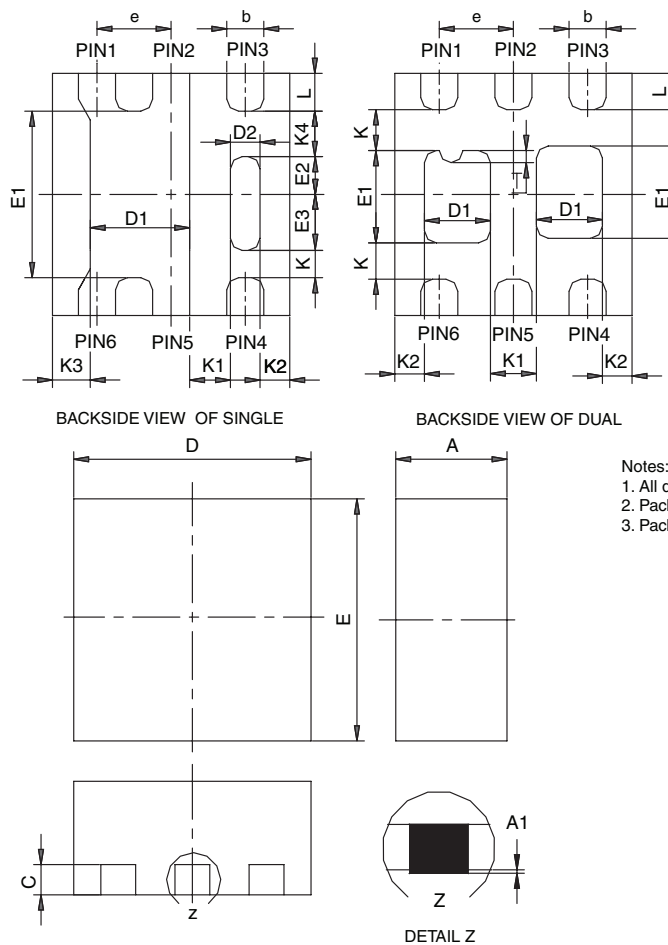
Vishay Siliconix

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62821.



PowerPAK® SC75-6L



- Notes:
1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
e	0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC		
K	0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP		
K1	0.275 TYP			0.011 TYP			0.320 TYP			0.013 TYP		
K2	0.200 TYP			0.008 TYP			0.200 BSC			0.008 TYP		
K3	0.255 TYP			0.010 TYP								
K4	0.300 TYP			0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

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DWG: 5935

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[Return to Index](#)



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